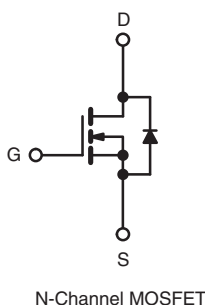
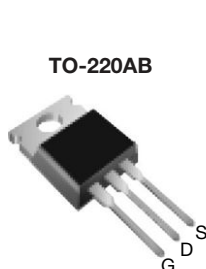


Power MOSFET

PRODUCT SUMMARY

V_{DS} (V) at T_J max.	560	
$R_{DS(on)}$ (Ω)	$V_{GS} = 10$ V	0.225
Q_g (Max.) (nC)	76	
Q_{gs} (nC)	21	
Q_{gd} (nC)	29	
Configuration	Single	



FEATURES

- Low Figure-of-Merit $R_{on} \times Q_g$
- 100 % Avalanche Tested
- High Peak Current Capability
- dV/dt Ruggedness
- Improved t_{rr}/Q_{rr}
- Improved Gate Charge
- High Power Dissipations Capability
- Compliant to RoHS Directive 2002/95/EC



Available
RoHS*
COMPLIANT

ORDERING INFORMATION

Package	TO-220AB
Lead (Pb)-free	SiHP18N50C-E3

ABSOLUTE MAXIMUM RATINGS ($T_C = 25^\circ\text{C}$, unless otherwise noted)

PARAMETER	SYMBOL	LIMIT	UNIT
Drain-Source Voltage	V_{DS}	500	V
Gate-Source Voltage	V_{GS}	± 30	
Continuous Drain Current ($T_J = 150^\circ\text{C}$) ^a	V_{GS} at 10 V	$T_C = 25^\circ\text{C}$	A
		$T_C = 100^\circ\text{C}$	
Pulsed Drain Current ^b	I_{DM}	72	
Linear Derating Factor	TO-220AB	1.8	W/ $^\circ\text{C}$
Single Pulse Avalanche Energy ^c	E_{AS}	361	mJ
Maximum Power Dissipation	TO-220AB	223	W
Peak Diode Recovery dV/dt ^d	dV/dt	5	V/ns
Operating Junction and Storage Temperature Range	T_J, T_{stg}	- 55 to + 150	$^\circ\text{C}$
Soldering Recommendations (Peak Temperature) ^d	for 10 s	300	

Notes

- Drain current limited by maximum junction temperature.
- Repetitive rating; pulse width limited by maximum junction temperature.
- $V_{DD} = 50$ V, starting $T_J = 25^\circ\text{C}$, $L = 2.5$ mH, $R_g = 25\ \Omega$, $I_{AS} = 17$ A.
- $I_{SD} \leq 18$ A, $dI/dt \leq 380$ A/ μs , $V_{DD} \leq V_{DS}$, $T_J \leq 150^\circ\text{C}$.
- 1.6 mm from case.

* Pb containing terminations are not RoHS compliant, exemptions may apply

THERMAL RESISTANCE RATINGS

PARAMETER		SYMBOL	TYP.	MAX.	UNIT
Maximum Junction-to-Ambient	TO-220	R_{thJA}	-	62	°C/W
Maximum Junction-to-Case (Drain)	TO-220	R_{thJC}	-	0.56	

SPECIFICATIONS ($T_J = 25\text{ °C}$, unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static							
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0\text{ V}$, $I_D = 250\text{ }\mu\text{A}$		500	-	-	V
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	Reference to $25\text{ }^{\circ}\text{C}$, $I_D = 1\text{ mA}$		-	0.6	-	V/ $^{\circ}\text{C}$
Gate-Source Threshold Voltage (N)	$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 250\text{ }\mu\text{A}$		3.0	-	5.0	V
Gate-Source Leakage	I_{GSS}	$V_{GS} = \pm 30\text{ V}$		-	-	± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 500\text{ V}$, $V_{GS} = 0\text{ V}$		-	-	25	μA
		$V_{DS} = 400\text{ V}$, $V_{GS} = 0\text{ V}$, $T_J = 125\text{ }^{\circ}\text{C}$		-	-	250	
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS} = 10\text{ V}$	$I_D = 10\text{ A}$	-	0.225	0.270	Ω
Forward Transconductance ^a	g_{fs}	$V_{DS} = 50\text{ V}$, $I_D = 10\text{ A}$		-	6.4	-	S
Dynamic							
Input Capacitance	C_{iss}	$V_{GS} = 0\text{ V}$, $V_{DS} = 25\text{ V}$, $f = 1.0\text{ MHz}$		-	2451	2942	pF
Output Capacitance	C_{oss}			-	300	360	
Reverse Transfer Capacitance	C_{rss}			-	26	32	
Internal Gate Resistance	R_g	$f = 1.0\text{ MHz}$, open drain		-	1.1	-	Ω
Total Gate Charge	Q_g	$V_{GS} = 10\text{ V}$	$I_D = 18\text{ A}$, $V_{DS} = 400\text{ V}$	-	65	76	nC
Gate-Source Charge	Q_{gs}			-	21	-	
Gate-Drain Charge	Q_{gd}			-	29	-	
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 250\text{ V}$, $I_D = 18\text{ A}$ $R_g = 7.5\text{ }\Omega$, $V_{GS} = 10\text{ V}$		-	80	-	ns
Rise Time	t_r			-	27	-	
Turn-Off Delay Time	$t_{d(off)}$			-	32	-	
Fall Time	t_f			-	44	-	
Drain-Source Body Diode Characteristics							
Continuous Source-Drain Diode Current	I_S	MOSFET symbol showing the integral reverse p - n junction diode 		-	-	18	A
Pulsed Diode Forward Current	I_{SM}			-	-	72	
Body Diode Voltage	V_{SD}	$T_J = 25\text{ }^{\circ}\text{C}$, $I_S = 18\text{ A}$, $V_{GS} = 0\text{ V}$		-	-	1.5	V
Body Diode Reverse Recovery Time	t_{rr}	$T_J = 25\text{ }^{\circ}\text{C}$, $I_F = I_S$, $dI/dt = 100\text{ A}/\mu\text{s}$, $V_R = 35\text{ V}$		-	503	-	ns
Body Diode Reverse Recovery Charge	Q_{rr}			-	6.7	-	μC
Reverse Recovery Current	I_{RRM}			-	30	-	A

Note

a. Repetitive rating; pulse width limited by maximum junction temperature.

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TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

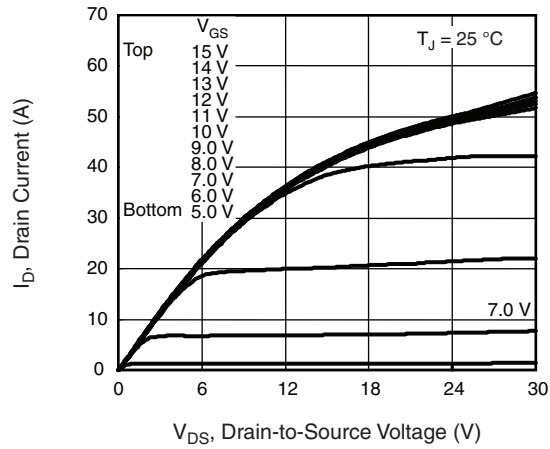


Fig. 1 - Typical Output Characteristics, $T_J = 150\text{ °C}$

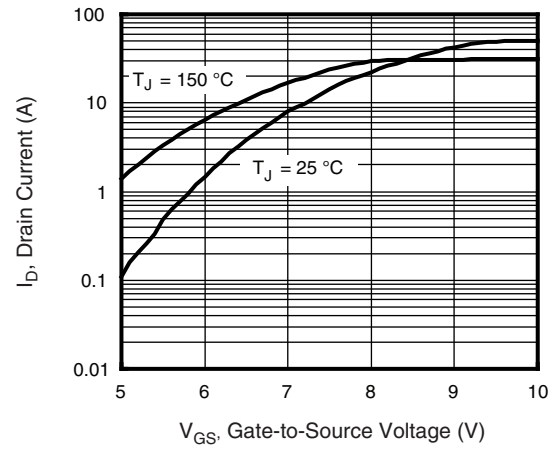


Fig. 3 - Typical Transfer Characteristics

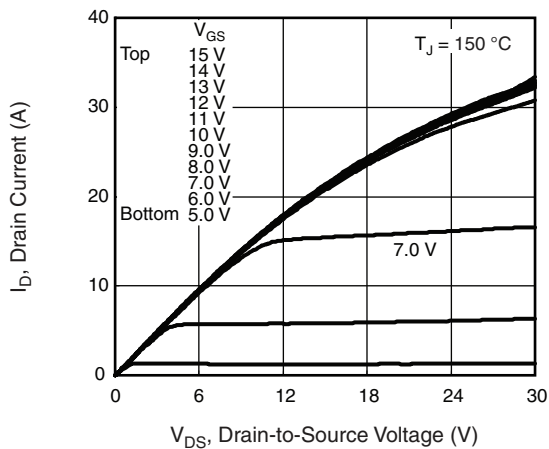


Fig. 2 - Typical Output Characteristics, $T_J = 150\text{ °C}$

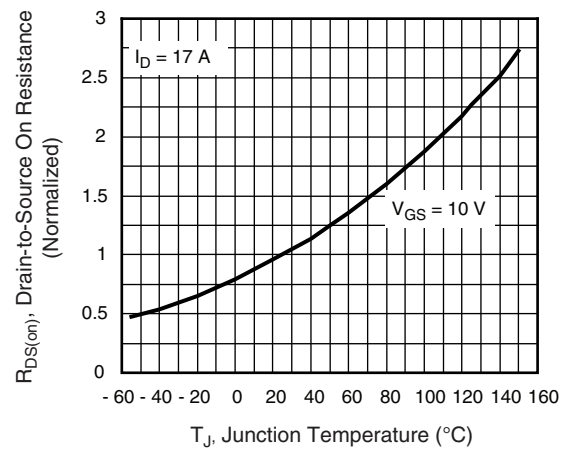


Fig. 4 - Normalized On-Resistance vs. Temperature

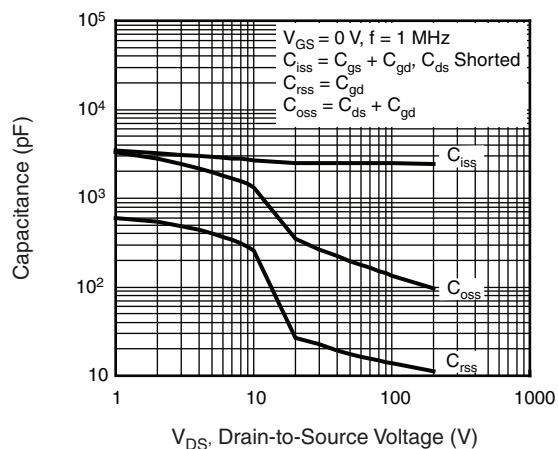


Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage

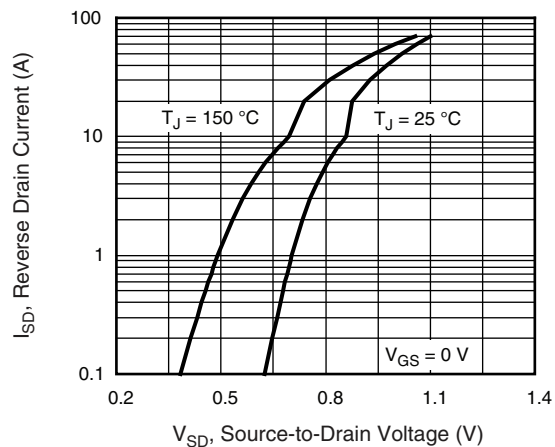


Fig. 7 - Typical Source-Drain Diode Forward Voltage

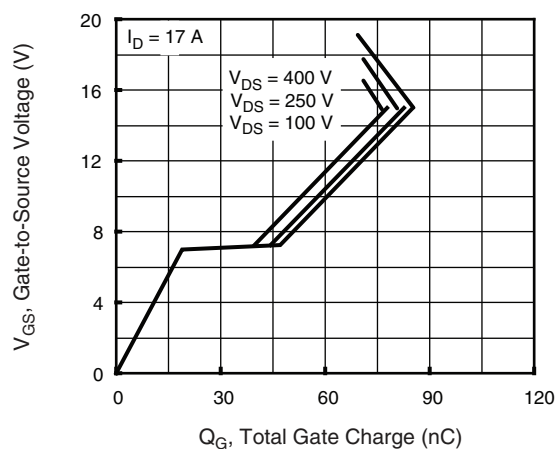


Fig. 6 - Typical Gate Charge vs. Gate-to-Source Voltage

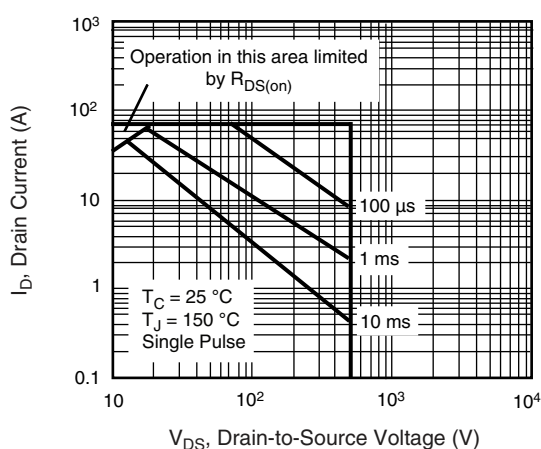


Fig. 8 - Maximum Safe Operating Area

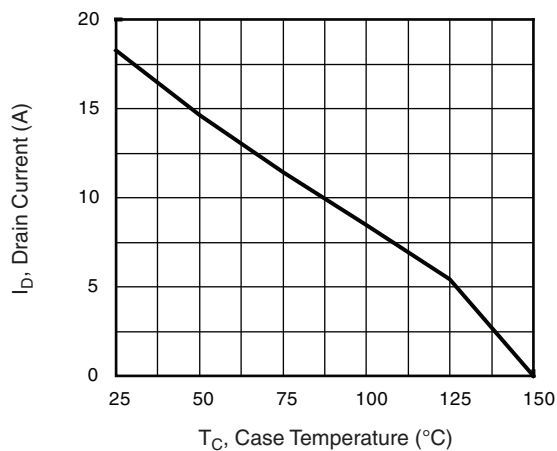


Fig. 9 - Maximum Drain Current vs. Case Temperature

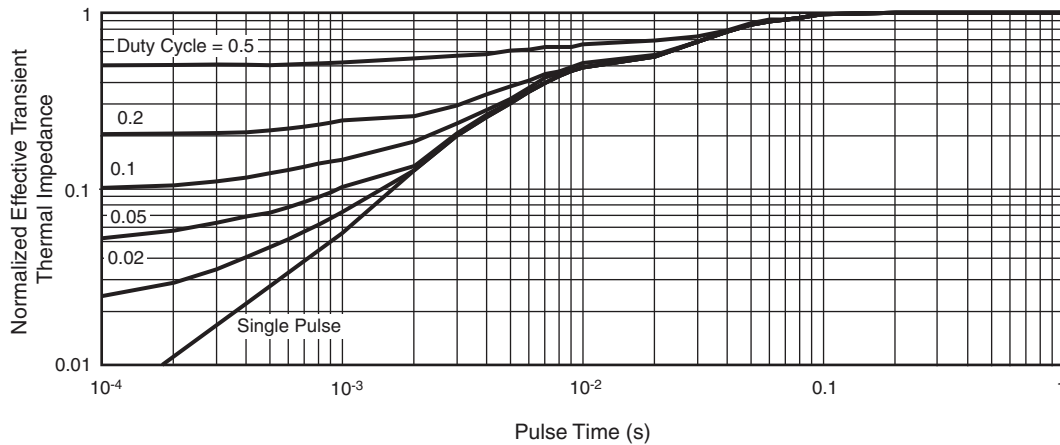


Fig. 10 - Normalized Thermal Transient Impedance, Junction-to-Case

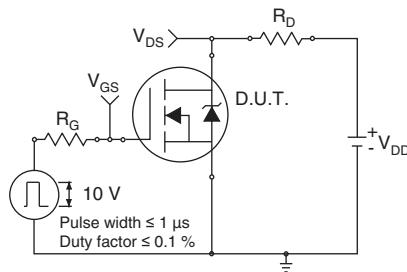


Fig. 11a - Switching Time Test Circuit

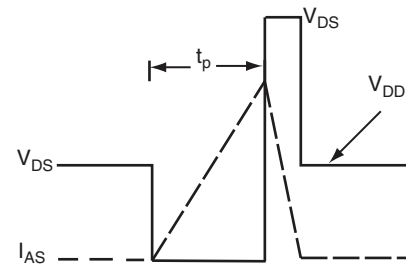


Fig. 12b - Unclamped Inductive Waveforms

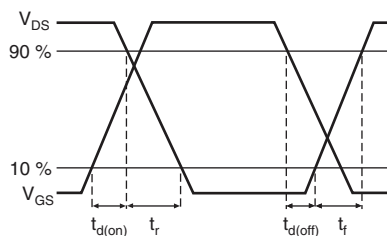


Fig. 11b - Switching Time Waveforms

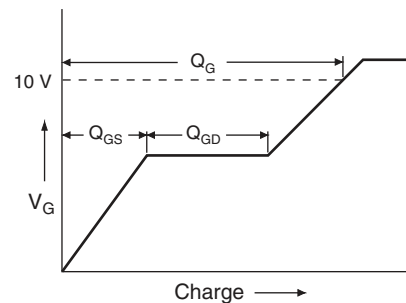


Fig. 13a - Basic Gate Charge Waveform

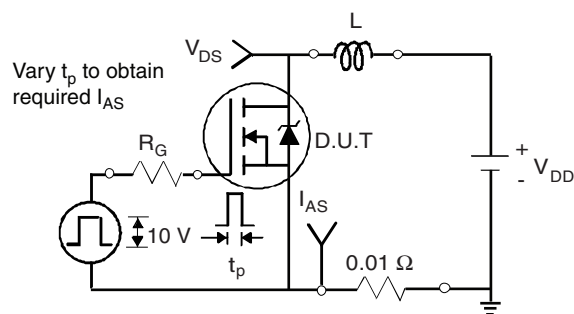


Fig. 12a - Unclamped Inductive Test Circuit

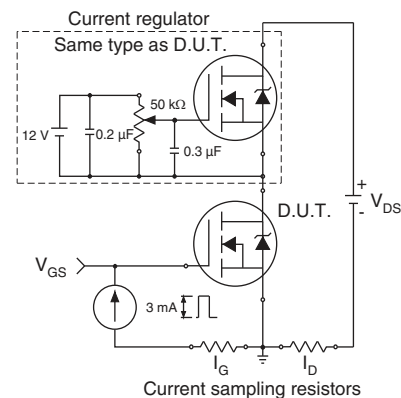
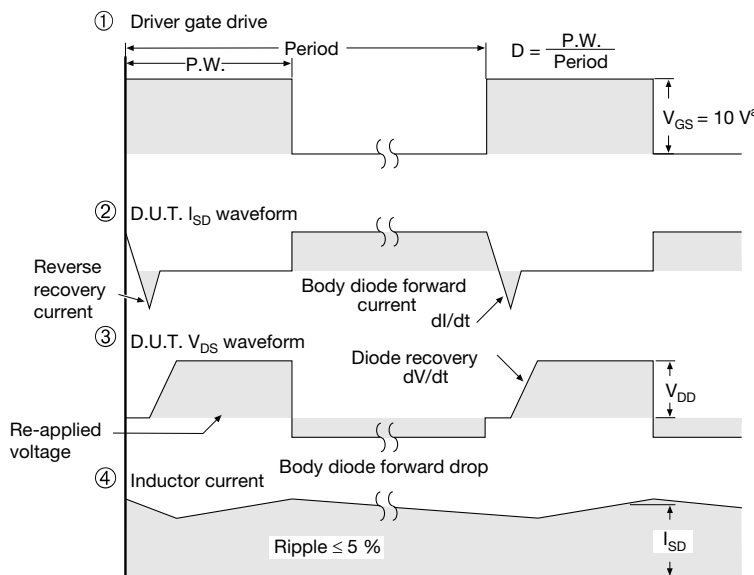
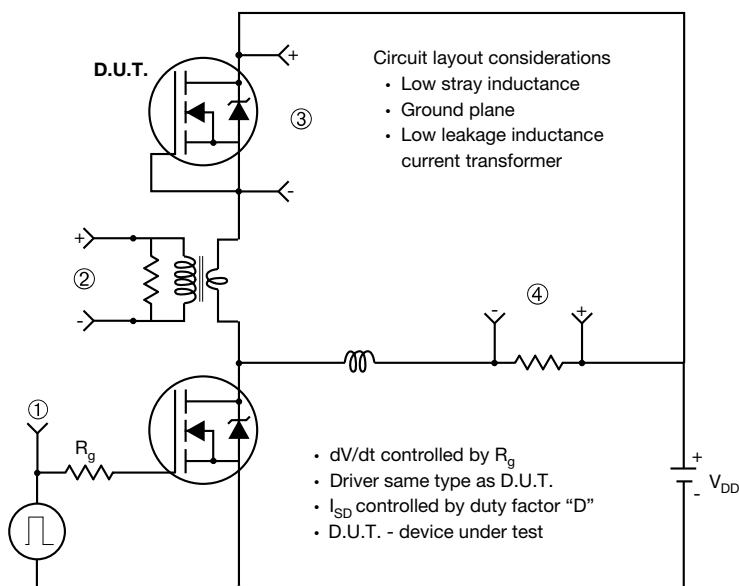


Fig. 13b - Gate Charge Test Circuit

Peak Diode Recovery dV/dt Test Circuit**Note**

a. $V_{GS} = 5\text{ V}$ for logic level devices

Fig. 14 - For N-Channel

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TO-220AB



DIM.	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	4.25	4.65	0.167	0.183
b	0.69	1.01	0.027	0.040
b(1)	1.20	1.73	0.047	0.068
c	0.36	0.61	0.014	0.024
D	14.85	15.49	0.585	0.610
E	10.04	10.51	0.395	0.414
e	2.41	2.67	0.095	0.105
e(1)	4.88	5.28	0.192	0.208
F	1.14	1.40	0.045	0.055
H(1)	6.09	6.48	0.240	0.255
J(1)	2.41	2.92	0.095	0.115
L	13.35	14.02	0.526	0.552
L(1)	3.32	3.82	0.131	0.150
$\varnothing P$	3.54	3.94	0.139	0.155
Q	2.60	3.00	0.102	0.118

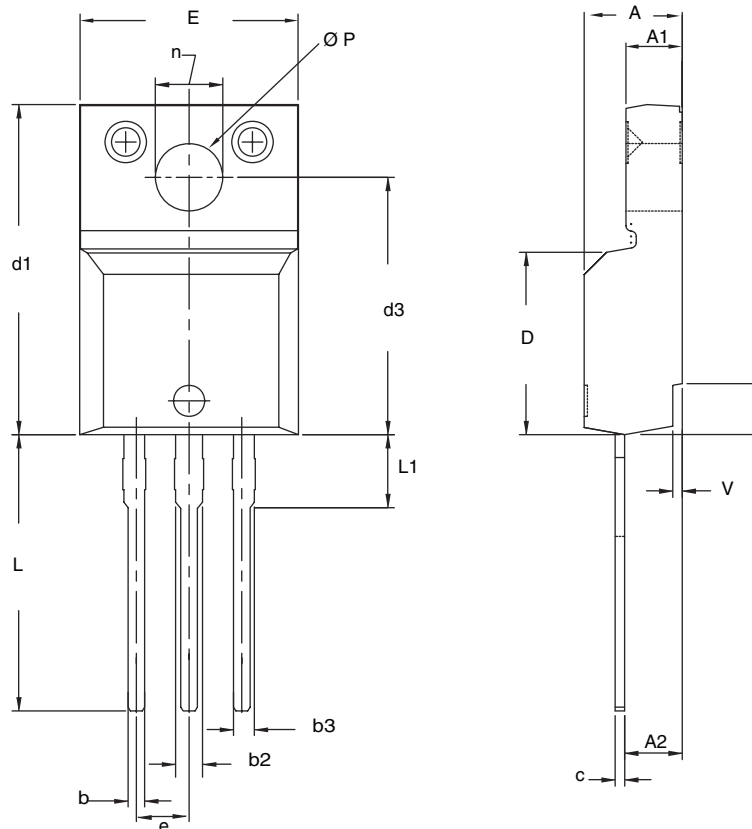
ECN: X12-0208-Rev. N, 08-Oct-12
DWG: 5471

Notes

- * $M = 1.32$ mm to 1.62 mm (dimension including protrusion)
Heatsink hole for HVM
- Xi'an and Mingxin actual photo



TO-220 FULLPAK (HIGH VOLTAGE)



DIM.	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	4.570	4.830	0.180	0.190
A1	2.570	2.830	0.101	0.111
A2	2.510	2.850	0.099	0.112
b	0.622	0.890	0.024	0.035
b2	1.229	1.400	0.048	0.055
b3	1.229	1.400	0.048	0.055
c	0.440	0.629	0.017	0.025
D	8.650	9.800	0.341	0.386
d1	15.88	16.120	0.622	0.635
d3	12.300	12.920	0.484	0.509
E	10.360	10.630	0.408	0.419
e	2.54 BSC		0.100 BSC	
L	13.200	13.730	0.520	0.541
L1	3.100	3.500	0.122	0.138
n	6.050	6.150	0.238	0.242
Ø P	3.050	3.450	0.120	0.136
u	2.400	2.500	0.094	0.098
v	0.400	0.500	0.016	0.020

ECN: X09-0126-Rev. B, 26-Oct-09
DWG: 5972

Notes

1. To be used only for process drawing.
2. These dimensions apply to all TO-220, FULLPAK leadframe versions 3 leads.
3. All critical dimensions should C meet $C_{pk} > 1.33$.
4. All dimensions include burrs and plating thickness.
5. No chipping or package damage.



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